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November 2013

FGH25N120FTDS 1200 V, 25 A Field Stop Trench IGBT

Features

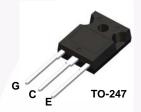
- High Speed Switching
- Low Saturation Voltage: V_{CE(sat)} = 1.60 V @ I_C = 25 A
- High Input Impedance
- RoHS Compliant

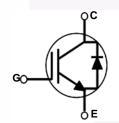
Applications

· Solar Inverter, UPS, Welder, PFC

General Description

Using advanced field stop trench technology, Fairchild's 1200V trench IGBTs offer the optimum performance for hard switching application such as solar inverter, UPS, welder and PFC applications.





Absolute Maximum Ratings

Symbol	Description		Ratings	Unit	
V _{CES}	Collector to Emitter Voltage		1200	V	
V _{GES}	Gate to Emitter Voltage		± 25	V	
I _C	Collector Current	$@ T_C = 25^{\circ}C$	50	A	
10	Collector Current	$@ T_C = 100^{\circ}C$	25	А	
I _{CM (1)}	Pulsed Collector Current		75	А	
l _F	Diode Continuous Forward Current	@ T _C = 25°C	50	A	
	Diode Continuous Forward Current @ T _C = 100°C		25	A	
I _{FM}	Diode Maximum Forward Current		75	A	
P _a	Maximum Power Dissipation	@ T _C = 25°C	313	W	
P_{D}	Maximum Power Dissipation @ $T_C = 100^{\circ}C$		125	W	
T _J	Operating Junction Temperature		-55 to +150	°C	
T _{stg}	Storage Temperature Range		-55 to +150	°C	
T _L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C	

Notes:
1: Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}(IGBT)$	R _{0JC} (IGBT) Thermal Resistance, Junction to Case		0.4	°C/W
$R_{\theta JC}(Diode)$	Thermal Resistance, Junction to Case	-	1.25	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	40	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGH25N120FTDS	FGH25N120FTDS	TO-247	Tube	N/A	N/A	30

Electrical Characteristics of the IGBT $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
BV _{CES}	Collector to Emitter Breakdown Voltage	$V_{GE} = 0 \text{ V}, I_{C} = 250 \mu A$	1200	-	-	V
I _{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}$, $V_{GE} = 0$ V	-	-	1	mA
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0 V$	-	-	±250	nA
On Charac	teristics					
V _{GE(th)}	G-E Threshold Voltage	I _C = 25 mA, V _{CE} = V _{GE}	3.5	6	7.5	V
		I _C = 25 A, V _{GE} = 15 V	-	1.6	2	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	$I_C = 25 \text{ A}, V_{GE} = 15 \text{ V},$ $T_C = 125^{\circ}\text{C}$	-	1.92	-	V
Dynamic C	haracteristics			1		
C _{ies}	Input Capacitance		-	4090	-	pF
C _{oes}	Output Capacitance	$V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$ f = 1 MHz	-	135	-	pF
C _{res}	Reverse Transfer Capacitance	- I = I WIMZ	-	75	-	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time		-	26	35	ns
t _r	Rise Time		-	41	53	ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 600 \text{ V}, I_{C} = 25 \text{ A},$ $R_{G} = 10 \Omega, V_{GE} = 15 \text{ V},$ Inductive Load, $T_{C} = 25^{\circ}\text{C}$	-	151	196	ns
t _f	Fall Time		-	102	132	ns
E _{on}	Turn-On Switching Loss		-	1.42	1.84	mJ
E _{off}	Turn-Off Switching Loss		-	1.16	1.5	mJ
E _{ts}	Total Switching Loss		-	2.58	3.34	mJ
t _{d(on)}	Turn-On Delay Time		- /	22	-	ns
t _r	Rise Time		-	41	-	ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 600 \text{ V}, I_{C} = 25 \text{ A},$	-	163	-	ns
t _f	Fall Time	$R_G = 10 \Omega$, $V_{GE} = 15 V$,	-	136	=	ns
E _{on}	Turn-On Switching Loss	Inductive Load, T _C = 125°C	-	2.04	-	mJ
E _{off}	Turn-Off Switching Loss		-	1.58	-	mJ
E _{ts}	Total Switching Loss		-	3.62	- //	mJ
Qg	Total Gate Charge		-	169	225	nC
Q _{ge}	Gate to Emitter Charge	$V_{CE} = 600 \text{ V}, I_{C} = 25 \text{ A},$ $V_{GE} = 15 \text{ V}$	-	33	44	nC
Q _{gc}	Gate to Collector Charge	▼GE - 13 V	-	78	104	nC

Electrical Characteristics of the Diode $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Тур.	Max	Unit
V _{FM}	Diode Forward Voltage	I _F = 25 A	$T_{\rm C} = 25^{\rm o}{\rm C}$	-	2.5	3.5	V
			$T_{\rm C} = 125^{\rm o}{\rm C}$	-	2.3	-	
t _{rr}	Diode Reverse Recovery Time		$T_C = 25^{\circ}C$	-	411	535	ns
	·	$I_F = 25 \text{ A},$ $di_F/dt = 200 \text{ A}/\mu\text{s}$	$T_{\rm C} = 125^{\rm o}{\rm C}$	-	496	-	110
I	Diode Peak Reverse Recovery Current		$T_C = 25^{\circ}C$	-	5.2	6.8	Α
ı _{rr}	Disact can revolve reservely carrein		$T_{\rm C} = 125^{\rm o}{\rm C}$	-	6.9	-]
0	Q _{rr} Diode Reverse Recovery Charge		$T_{\rm C} = 25^{\rm o}{\rm C}$	-	1.1	1.82	μС
~II			$T_{\rm C} = 125^{\rm o}{\rm C}$	-	1.7	-	

Figure 1. Typical Output Characteristics

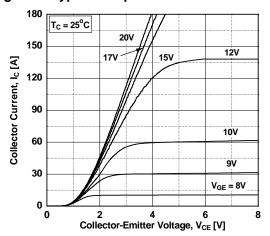


Figure 3. Typical Saturation Voltage Characteristics

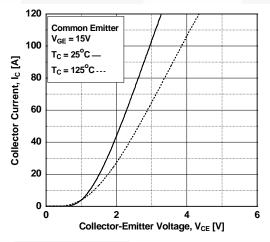


Figure 5. Saturation Voltage vs. Case
Temperature at Variant Current Level

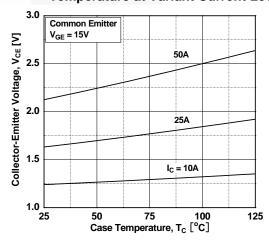


Figure 2. Typical Output Characteristics

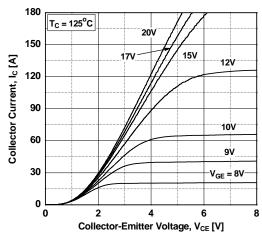


Figure 4. Transfer Characteristics

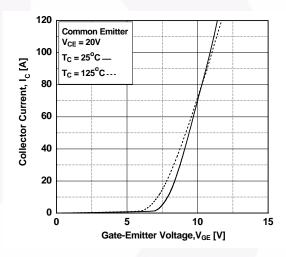


Figure 6. Saturation Voltage vs. V_{GE}

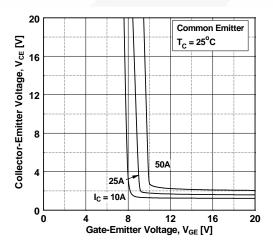


Figure 7. Saturation Voltage vs. V_{GE}

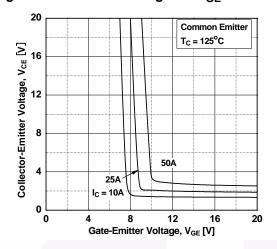


Figure 8. Load Current vs. Frequency

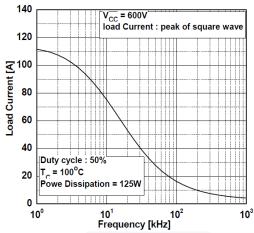


Figure 9. Capacitance Characteristics

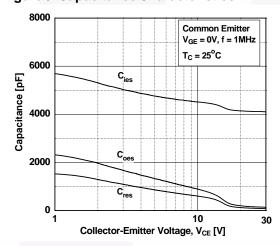


Figure 10. Gate Charge Characteristics

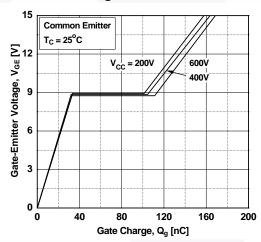


Figure 11. SOA Characteristics
Gate Resistance

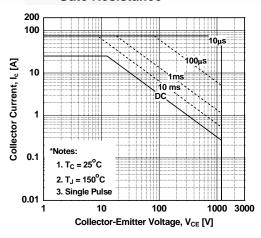


Figure 12. Turn-on Characteristics vs.
Gate Resistance

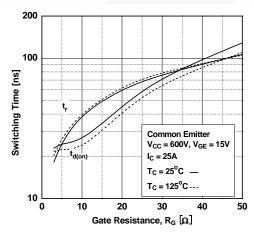


Figure 13. Turn-off Characteristics vs.
Gate Resistance

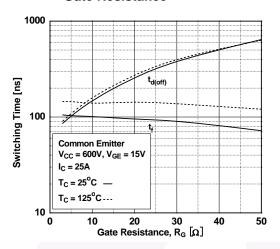


Figure 15. Turn-off Characteristics vs. Collector Current

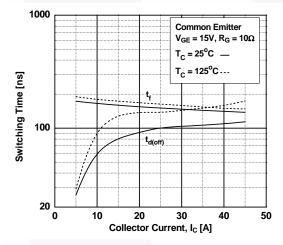


Figure 17. Switching Loss vs. Collector Current

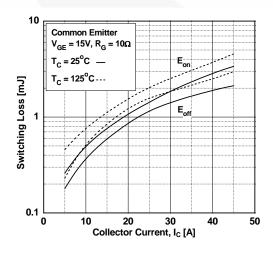


Figure 14. Turn-on Characteristics vs. Collector Current

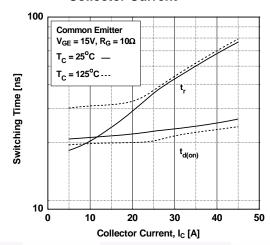


Figure 16. Switching Loss vs. Gate Resistance

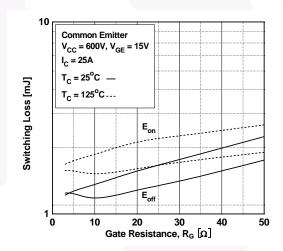


Figure 18. Turn off Switing SOA Characteristics

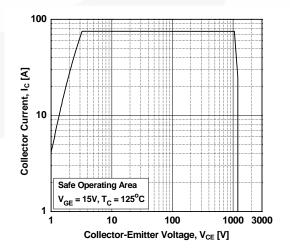


Figure 19. Forward Characteristics

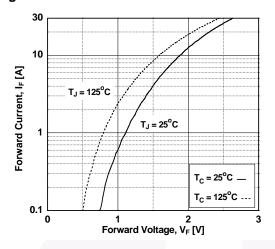


Figure 20. Reverse Recovery Current

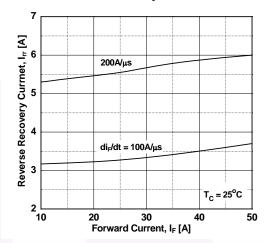


Figure 21. Stored Charge

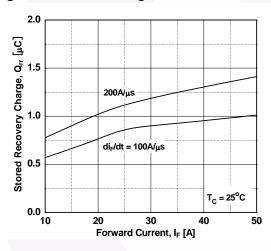


Figure 22. Reverse Recovery Time

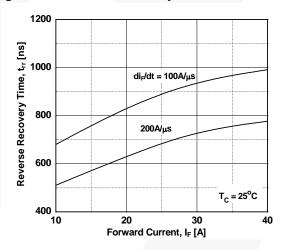
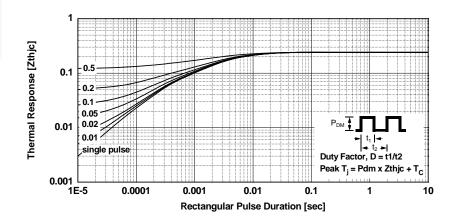


Figure 23. Transient Thermal Impedance of IGBT



Mechanical Dimensions В 15.87 E φ^{3.65}/_{3.51}/_E Φ 0.254 Μ Β ΑΜ 12.81 E $\phi_{3.51}^{3.65}$ 5.58 E 1.35 Ø 5.20 F 13.08 MIN 3 16.25 E (1.60) 3 2.66 5.56 11.12 NOTES: UNLESS OTHERWISE SPECIFIED. A. PACKAGE REFERENCE: JEDEC TO-247, ISSUE E, VARIATION AB, DATED JUNE, 2004. B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS. ALL DIMENSIONS ARE IN MILLIMETERS. D. DRAWING CONFORMS TO ASME Y14.5 - 1994 DOES NOT COMPLY JEDEC STANDARD VALUE

Figure 24. TO-247 3L - TO-247, MOLDED, 3 LEAD, JEDEC VARIATION AB

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